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72.

- A single crystal GaN substrate grown on a gallium arsenide substrate followed by etching of the gallium arsenide to yield the GaN single crystal substrate free of defects caused by thermal coefficient of expansion differences.
  - The GaN single crystal substrate of claim 12, wherein the GaN single crystal substrate is of three dimensional (x,y,z) character wherein each of the dimensions x, y is at least 100 micrometers and the dimension z is at least 1 micrometer.
- 74. The GaN single crystal substrate of claim 72, having a thickness of from 1 to 1,000 micrometers.
- 75. A device structure including a device fabricated on a GaN single crystal substrate as in claim 72.
- The device structure of claim 7b, wherein the device is selected from the group consisting 76. of LEDs, lasers, detectors, and transistors, and device precursor structures thereof.

## REMARKS

The claims added and now pending in this continuation application are claims 39-76 set out above.

Concurrently submitted herewith is a petition for three months extension of time in parent Application No. 08/955,168.

Respectfully submitted,

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